



## 50V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 50 V Current 350mA

#### **Features**

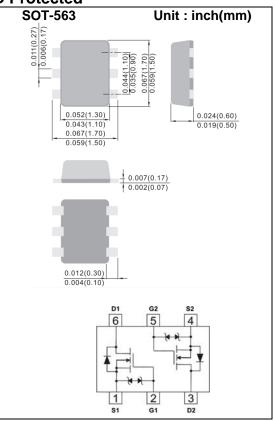
- RDS(ON), VGS@10V, ID@500mA<1.6Ω
- RDS(ON) , VGS@4.5V, ID@200mA<2.5Ω</li>
- RDS(ON) , VGS@2.5V, ID@100mA<4.5Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc.
- ESD Protected
- Lead free in comply with EU RoHS 2011/65/EU directives.
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

• Case: SOT-563 Package

Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	50	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	350	mA
Pulsed Drain Current		I <sub>DM</sub>	1200	mA
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	223	mW
	Derate above 25°C		1.8	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	560	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	50	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.8	1.0	1.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =500mA	-	0.93	1.6	Ω
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA	-	1.2	2.5	
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =100mA	-	2.4	4.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	<u>+</u> 3.0	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =25V, I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.63	1	nC
Gate-Source Charge	$Q_gs$		-	0.2	-	
Gate-Drain Charge	$Q_gd$		-	0.23	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	-	50	pF
Output Capacitance	Coss		-	-	10	
Reverse Transfer Capacitance	Crss	I=1.UIVIDZ	-	-	5	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	\/ -05\/   -500A	-	2.2	5	
Turn-On Rise Time	tr	$V_{DD}$ =25V, $I_{D}$ =500mA, $V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 1.2)		19.2	38	ns
Turn-Off Delay Time	td <sub>(off)</sub>			6.2	12	
Turn-Off Fall Time	tf		-	23	50	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>		-	_	500	mA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V		0.86	1.5	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper





#### **TYPICAL CHARACTERISTIC CURVES**

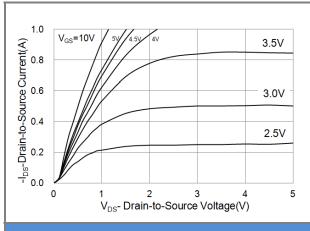
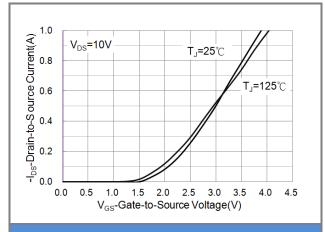


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

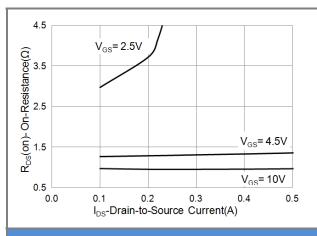


Fig.3 On-Resistance vs. Drain Current

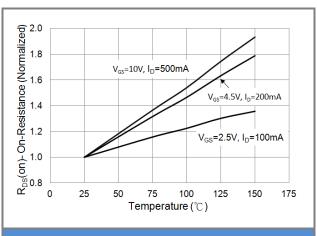


Fig.4 On-Resistance vs. Junction temperature

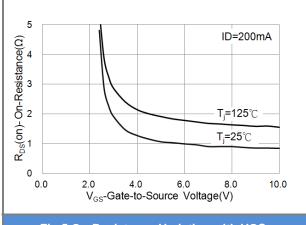


Fig.5 On-Resistance Variation with VGS.

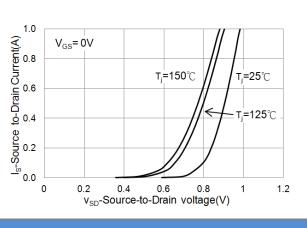


Fig.6 Body Dlode CharacterIslcs





### **TYPICAL CHARACTERISTIC CURVES**

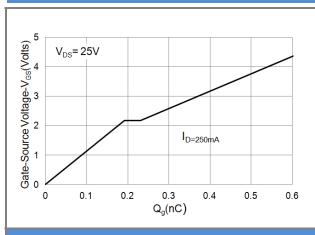


Fig.7 Gate-Charge Characteristics

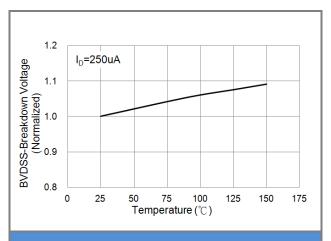


Fig.8 Breakdown Voltage Variation vs. Temperature

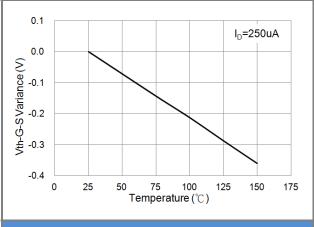


Fig.9 Threshold Voltage Variation with Temperature.

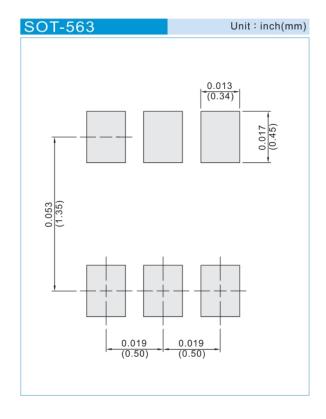




### **ORDER INFORMATION**

Order Part Number	Package Type	Packing type	Marking	Version
PJX138K_R1_00001	SOT-563	4K pcs / 7" reel	8KB	Halogen free
PJX138K_R2_00001	SOT-563	10K pcs / 13" reel	8KB	Halogen free

### **MOUNTING PAD LAYOUT**







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